

5008: Computer Architecture

Chapter 5 - Memory Hierarchy Design

CA Lecture10 - memory hierarchy design (cwliu@twins.ee.nctu.edu.tw)

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Outline



- 11 Advanced Cache Optimizations
- Memory Technology and DRAM Optimizations
- Virtual Machines
- Conclusion







Why More on Memory Hierarchy?





Review: 6 Basic Cache Optimizations

- Reducing hit time
- 1. Giving Reads Priority over Writes
 - E.g., Read complete before earlier writes in write buffer
- 2. Avoiding Address Translation during Cache Indexing
- Reducing Miss Penalty
- 3. Multilevel Caches
- Reducing Miss Rate
- 4. Larger Block size (Compulsory misses)
- 5. Larger Cache size (Capacity misses)
- 6. Higher Associativity (Conflict misses)





11 Advanced Cache Optimizations

- Reducing hit time
- 1. Small and simple caches
- 2. Way prediction
- 3. Trace caches
- Increasing cache bandwidth
- 4. Pipelined caches
- 5. Multibanked caches
- 6. Nonblocking caches

- Reducing Miss Penalty
- 7. Critical word first
- 8. Merging write buffers
- Reducing Miss Rate
- 9. Compiler optimizations
- Reducing miss penalty or miss rate via parallelism
 10.Hardware prefetching
 11.Compiler prefetching

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1. Fast Hit times via Small and Simple Caches

- Index tag memory and then compare takes time
- \Rightarrow Small cache can help hit time since smaller memory takes less time to index
 - E.g., L1 caches same size for 3 generations of AMD microprocessors:
 K6, Athlon, and Opteron
 - Also L2 cache small enough to fit on chip with the processor avoids time penalty of going off chip
- Simple \Rightarrow direct mapping
 - Can overlap tag check with data transmission since no choice
- Access time estimate for 90 nm using CACTI model 4.0
 - Median ratios of access time relative to the direct-mapped caches are
 1.32, 1.39, and 1.43 for 2-way, 4-way, and 8-way caches







2. Fast Hit times via Way Prediction

- How to combine fast hit time of Direct Mapped and have the lower conflict misses of 2-way SA cache?
- Way prediction: keep extra bits in cache to predict the "way," or block within the set, of next cache access.
 - Multiplexor is set early to select desired block, only 1 tag comparison performed that clock cycle in parallel with reading the cache data
 - Miss $\Rightarrow 1^{s\dagger}$ check other blocks for matches in next clock cycle

Hit Time

Way-Miss Hit Time

Miss Penalty

- Accuracy $\approx 85\%$
- Drawback: CPU pipeline is hard if hit takes 1 or 2 cycles
 - Used for instruction caches vs. data caches

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3. Fast Hit times via Trace Cache

- Find more instruction level parallelism? How avoid translation from x86 to microops?
- Trace cache in Pentium 4
- 1. Dynamic traces of the executed instructions vs. static sequences of instructions as determined by layout in memory
 - Built-in branch predictor
- 2. Cache the micro-ops vs. x86 instructions
 - Decode/translate from x86 to micro-ops on trace cache miss
- + 1. \Rightarrow better utilize long blocks (don't exit in middle of block, don't enter at label in middle of block)
- 1. \Rightarrow complicated address mapping since addresses no longer aligned to power-of-2 multiples of word size
- 1. \Rightarrow instructions may appear multiple times in multiple dynamic traces due to different branch outcomes





4: Increasing Cache Bandwidth by Pipelining

- Pipeline cache access to maintain bandwidth, but higher latency
- Instruction cache access pipeline stages:
 - 1: Pentium
 - 2: Pentium Pro through Pentium III
 - 4: Pentium 4
- \Rightarrow greater penalty on mispredicted branches
- \Rightarrow more clock cycles between the issue of the load and the use of the data



5. Increasing Cache Bandwidth: Non-Blocking Caches

- <u>Non-blocking cache</u> or <u>lockup-free cache</u> allow data cache to continue to supply cache hits during a miss
 - requires F/E bits on registers or out-of-order execution
 - requires multi-bank memories
- "<u>hit under miss</u>" reduces the effective miss penalty by working during miss vs. ignoring CPU requests
- "<u>hit under multiple miss</u>" or "<u>miss under miss</u>" may further lower the effective miss penalty by overlapping multiple misses
 - Significantly increases the complexity of the cache controller as there can be multiple outstanding memory accesses
 - Requires muliple memory banks (otherwise cannot support)
 - Penium Pro allows 4 outstanding memory misses





: Increasing Cache Bandwidth via Multiple Banks



- Rather than treat the cache as a single monolithic block, divide into independent banks that can support simultaneous accesses
 - E.g., T1 ("Niagara") L2 has 4 banks
- Banking works best when accesses naturally spread themselves across banks ⇒ mapping of addresses to banks affects behavior of memory system
- Simple mapping that works well is "sequential interleaving"
 - Spread block addresses sequentially across banks
 - E,g, if there 4 banks, Bank 0 has all blocks whose address modulo 4 is 0; bank 1 has all blocks whose address modulo 4 is



- Don't wait for full block before restarting CPU
- <u>Early restart</u>—As soon as the requested word of the block arrives, send it to the CPU and let the CPU continue execution
 - Spatial locality \Rightarrow tend to want next sequential word, so not clear size of benefit of just early restart
- <u>Critical Word First</u>—Request the missed word first from memory and send it to the CPU as soon as it arrives; let the CPU continue execution while filling the rest of the words in the block
 - Long blocks more popular today \Rightarrow Critical Word 1st Widely used

block





8. Merging Write Buffer to Reduce Miss Penalty



- Write buffer to allow processor to continue while waiting to write to memory
- If buffer contains modified blocks, the addresses can be checked to see if address of new data matches the address of a valid write buffer entry
- If so, new data are combined with that entry
- Increases block size of write for write-through cache of writes to sequential words, bytes since multiword writes more efficient to memory
- The Sun T1 (Niagara) processor, among many others, uses write merging



OF ELECTRONICS Configurations Compiler

- McFarling [1989] reduced caches misses by 75% on 8KB direct mapped cache, 4 byte blocks <u>in software</u>
- Instructions
 - Reorder procedures in memory so as to reduce conflict misses
 - Profiling to look at conflicts(using tools they developed)
- Data
 - Merging Arrays: improve spatial locality by single array of compound elements vs. 2 arrays
 - Loop Interchange: change nesting of loops to access data in order stored in memory
 - Loop Fusion: Combine 2 independent loops that have same looping and some variables overlap
 - Blocking: Improve temporal locality by accessing "blocks" of data repeatedly vs. going down whole columns or rows







Merging Arrays Example

/* Before: 2 sec	quential arrays */	
<pre>int val[SIZE];</pre>	val	key
<pre>int key[SIZE];</pre>		
<pre>/* After: 1 arra struct merge { int val; int key; }; struct merge mer</pre>	ay of stuctures */ <pre>valkeyvalkey</pre> valkeyalkey	

Reducing conflicts between val & key; improve spatial locality



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Loop Interchange Example

Sequential accesses instead of striding through memory every 100 words; improved spatial locality



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Loop Fusion Example

```
/* Before */
for (i = 0; i < N; i = i+1)
  for (j = 0; j < N; j = j+1)
       a[i][j] = 1/b[i][j] * c[i][j];
for (i = 0; i < N; i = i+1)
  for (j = 0; j < N; j = j+1)</pre>
      d[i][j] = a[i][j] + c[i][j];
/* After */
for (i = 0; i < N; i = i+1)
  for (j = 0; j < N; j = j+1)
       a[i][j] = 1/b[i][j] * c[i][j];
  {
       d[i][j] = a[i][j] + c[i][j];
```



Perform different computations on the common data in two loops → fuse the two loops

2 misses per access to a & $_{\rm C}$ vs. one miss per access; improve spatial locality

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Blocking Example

```
/* Before */
for (<u>i</u> = 0; i < N; i = i+1)
  for (j = 0; j < N; j = j+1)
    {r = 0;
    for (k = 0; k < N; k = k+1){
        r = r + y[i][k]*z[k][j];};
        x[i][j] = r;
    };</pre>
```

- Two Inner Loops:
 - Read all NxN elements of z[]
 - Read N elements of 1 row of y[] repeatedly
 - Write N elements of 1 row of x[]
- Capacity Misses a function of N & Cache Size:
 - $-2N^3 + N^2 =$ (assuming no conflict; otherwise ...)

• compute on BxB submatrix that fits





Snapshot of x, y, z when i=1





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Blocking Example

- B called *Blocking Factor*
- Capacity Misses from $2N^3 + N^2$ to $2N^3/B + N^2$

Sonflict Misses Too?

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The Age of Accesses to x, y, z



Note in contrast to previous Figure, the smaller number of elements accessed



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10. Reducing Misses by <u>Hardware</u> Prefetching of Instructions & Data

- Prefetching relies on having extra memory bandwidth that can be used without penalty
- Instruction Prefetching
 - Typically, CPU fetches 2 blocks on a miss: the requested block and the next consecutive block.
 - Requested block is placed in instruction cache when it returns, and prefetched block is placed into instruction stream buffer
- Data Prefetching
 - Pentium 4 can prefetch data into L2 cache from up to 8 streams from 8 different 4 KB pages
 - Prefetching invoked if 2 successive L2 cache misses to a page, if distance between those cache blocks is < 256 bytes





DEDITION OF ELECTRONICS IN 11. Reducing Misses by Software Prefetching Data

- Data Prefetch
 - Load data into register (HP PA-RISC loads)
 - Cache Prefetch: load into cache (MIPS IV, PowerPC, SPARC v. 9)
 - Special prefetching instructions cannot cause faults; a form of speculative execution
- Issuing Prefetch Instructions takes time
 - Is cost of prefetch issues < savings in reduced misses?</p>
 - Higher superscalar reduces difficulty of issue bandwidth





Compiler Optimization vs. Memory Hierarchy Search



- Compiler tries to figure out memory hierarchy optimizations
- New approach: "Auto-tuners" 1st run variations of program on computer to find best combinations of optimizations (blocking, padding, ...) and algorithms, then produce C code to be compiled for *that* computer
- "Auto-tuner" targeted to numerical method
 - E.g., PHiPAC (BLAS), Atlas (BLAS),
 Sparsity (Sparse linear algebra), Spiral (DSP), FFT-W



Technique	Hit Time	Band- width	Mi ss pe na lt y	Mis s rat e	HW cost/ complexi ty	Comment
Small and simple caches	+			_	0	Trivial; widely used
Way-predicting caches	+				1	Used in Pentium 4
Trace caches	+				3	Used in Pentium 4
Pipelined cache access	_	+			1	Widely used
Nonblocking caches		+	+		3	Widely used
Banked caches		+			1	Used in L2 of Opteron and Niagara
Critical word first and early restart			+		2	Widely used
Merging write buffer			+		1	Widely used with write through
Compiler techniques to reduce cache misses				+	0	Software is a challenge; some computers have compiler option
Hardware prefetching of instructions and data			+	+	2 instr., <mark>3</mark> data	Many prefetch instructions; AMD Opteron prefetches data
Compiler-controlled prefetching			+	+	3	Needs nonblocking cache; in many CPUs



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of ELECTRONICS IN A Main Memory Background

- Performance of Main Memory:
 - Latency: Cache Miss Penalty
 - Access Time: time between request and word arrives
 - Cycle Time: time between requests
 - <u>Bandwidth</u>: I/O & Large Block Miss Penalty (L2)
- Main Memory is *DRAM*: Dynamic Random Access Memory
 - Dynamic since needs to be refreshed periodically (8 ms, 1% time)
 - Addresses divided into 2 halves (Memory as a 2D matrix):
 - RAS or Row Access Strobe
 - CAS or Column Access Strobe
- Cache uses *SRAM*: Static Random Access Memory
 - No refresh (6 transistors/bit vs. 1 transistor Size: DRAM/SRAM - 4-8, Cost/Cycle time: SRAM/DRAM - 8-16







Main Memory Deep Background

- "Out-of-Core", "In-Core," "Core Dump"?
- "Core memory"?
- Non-volatile, magnetic
- Lost to 4 Kbit DRAM (today using 512Mbit DRAM)
- Access time 750 ns, cycle time 1500-3000 ns







DRAM logical organization (4 Mbit)





Square root of bits per RAS/CAS

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Quest for DRAM Performance

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- 1. Fast Page mode
 - Add timing signals that allow repeated accesses to row buffer without another row access time
 - Such a buffer comes naturally, as each array will buffer 1024 to 2048 bits for each access
- 2. Synchronous DRAM (SDRAM)
 - Add a clock signal to DRAM interface, so that the repeated transfers would not bear overhead to synchronize with DRAM controller
- 3. Double Data Rate (DDR SDRAM)
 - Transfer data on both the rising edge and falling edge of the DRAM clock signal \Rightarrow doubling the peak data rate
 - DDR2 lowers power by dropping the voltage from 2.5 to 1.8 volts + offers higher clock rates: up to 400 MHz
 - DDR3 drops to 1.5 volts + higher clock rates: up to 800 MHz
 - Improved Bandwidth, not Latency

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DRAM name based on Peak Chip Transfers / Sec DIMM name based on Peak DIMM MBytes / Sec

	Stan- dard	Clock Rate (MHz)	M transfers / second	DRAM Name	Mbytes/s/ DIMM	DIMM Name
	DDR	133	266	DDR266	2128	PC2100
B)	DDR	150	300	DDR300	2400	PC2400
25/G	DDR	200	400	DDR400	3200	PC3200
6 (\$1	DDR2	266	533	DDR2-533	4264	PC4300
le 4/0	DDR2	333	667	DDR2-667	5336	PC5300
or sa	DDR2	400	800	DDR2-800	6400	PC6400
itest f	DDR3	533	1066	DDR3-1066	8528	PC8500
Fas	DDR3	666	1333	DDR3-1333	10664	PC10700
	DDR3	800	1600	DDR3-1600	12800	PC12800
		x 2		× 8		10-32



Need for Error Correction!

- Motivation:
 - Failures/time proportional to number of bits!
 - As DRAM cells shrink, more vulnerable
- Went through period in which failure rate was low enough without error correction that people didn't do correction
 - DRAM banks too large now
 - Servers always corrected memory systems
- Basic idea: add redundancy through parity bits
 - Common configuration: Random error correction
 - SEC-DED (single error correct, double error detect)
 - One example: 64 data bits + 8 parity bits (11% overhead)
 - Really want to handle failures of physical components as well
 - Organization is multiple DRAMs/DIMM, multiple DIMMs
 - Want to recover from failed DRAM and failed DIMM!
 - "Chip kill" handle failures width of single DRAM chip





DRAM Technology

- Semiconductor Dynamic Random Access Memory
- Emphasize on cost per bit and capacity
- Multiplex address lines → cutting # of address pins in half
 - Row access strobe (RAS) first, then column access strobe (CAS)
 - Memory as a 2D matrix rows go to a buffer
 - Subsequent CAS selects subrow
- Use only a single transistor to store a bit
 - Reading that bit can destroy the information
 - Refresh each bit periodically (ex. 8 milliseconds) by writing back
 - Keep refreshing time less than 5% of the total time
- DRAM capacity is 4 to 8 times that of SRAM







DRAM Technology (Cont.)

- DIMM: Dual inline memory module
 - DRAM chips are commonly sold on small boards called DIMMs
 - DIMMs typically contain 4 to 16 DRAMs
- Slowing down in DRAM capacity growth
 - Four times the capacity every three years, for more than 20 years
 - New chips only double capacity every two year, since 1998
- DRAM performance is growing at a slower rate
 - RAS (related to latency): 5% per year
 - CAS (related to bandwidth): 10%+ per year





RAS improvement

Chip size				Cycle time (ns)
	Slowest DRAM (ns)	Fastest DRAM (ns)	Column access strobe (CAS)/ data transfer time (ns)	
64K bit	180	150	75	250
256K bit	150	120	50	220
1M bit	120	100	25	190
4M bit	100	80	20	165
16M bit	80	60	15	120
64M bit	70	50	12	110
109M bit	70	50	10	100
126M bit	65	45	7	90
512M bit	60	40	5	80
	Chip size 64K bit 256K bit 1M bit 4M bit 16M bit 128M bit 256M bit 512M bit	Slowest DRAM (ns) 64K bit 180 256K bit 150 1M bit 120 4M bit 100 16M bit 80 64M bit 70 128M bit 70 256M bit 65 512M bit 60	Slowest DRAM (ns)Fastest DRAM (ns)64K bit180150256K bit1501201M bit1201004M bit1008016M bit806064M bit7050128M bit7050256M bit6545512M bit6040	Chip sizeSlowest DRAM (ns)Fastest DRAM (ns)Column access strobe (CAS)/ data transfer time (ns)64K bit18015075256K bit150120501M bit120100254M bit100802016M bit80601564M bit705012128M bit705010256M bit65457512M bit60405

A performance improvement in RAS of about 5% per year



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SRAM Technology

- Cache uses SRAM: Static Random Access Memory
- SRAM uses six transistors per bit to prevent the information from being disturbed when read
 - \rightarrow no need to refresh

 - No difference between access time and cycle time for SRAM
- Emphasize on speed and capacity
 - SRAM address lines are not multiplexed
- SRAM speed is 8 to 16x that of DRAM





ROM and Flash

- Embedded processor memory
- Read-only memory (ROM)
 - Programmed at the time of manufacture
 - Only a single transistor per bit to represent 1 or 0
 - Used for the embedded program and for constant
 - Nonvolatile and indestructible
- Flash memory:
 - Nonvolatile but allow the memory to be modified
 - Reads at almost DRAM speeds, but writes 10 to 100 times slower
 - DRAM capacity per chip and MB per dollar is about 4 to 8 times greater than flash





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- Fast page mode: time signals that allow repeated accesses to buffer without another row access time
- Synchronous RAM (SDRAM): add a clock signal to DRAM interface, so that the repeated transfer would not bear overhead to synchronize with the controller
 - Asynchronous DRAM involves overhead to sync with controller
 - Peak speed per memory module 800—1200MB/sec in 2001
- Double data rate (DDR): transfer data on both the rising edge and falling edge of DRAM clock signal
 - Peak speed per memory module 1600—2400MB/sec in 2001





RAMBUS



- RAMBUS optimizes the interface between DRAM and CPU
- RAMBUS makes a single chip act more like a memory system than a memory component
 - Each chip has interleaved memory and high-speed interface
- 1st generation RAMBUS: RDAM
 - Replace RAS/CAS with a bus that allows other accesses over it between the sending of the address and return of the data
 - Each chip has four banks, each with their own row buffer
 - A chip can return a variable amount of data from a single request, and even perform its refresh
 - Clock signal and transfer on both edges of its clock
 - 300 MHz clock







RAMBUS (Cont.)

- 2nd generation RAMBUS: direct RDRAM (DRDRAM)
 - Offer up to 1.6GB/sec of bandwidth
 - Separate row- and column-command buses
 - 18-bit data bus; 16 internal banks; 8 row buffers; 400 MHz
- RAMBUS are sold in RIMMs: one RAMBUS chip per RIMM
- RAMBUS vs. DDR SDRAM
 - DIMM bandwidth (multiple DRAM chips) is closer to RAMBUS
 - RDRAM and DRDRAM have a price premium over traditional DRAM
 - Larger chips
 - In 2001, it is factor of 2





